

# **Darlington Transistors PNP Silicon**

#### **MAXIMUM RATINGS**

Rating	Symbol	MPSA62	MPSA63 MPSA64	Unit
Collector–Emitter Voltage	V <sub>CES</sub>	-20	-30	Vdc
Collector-Base Voltage	V <sub>CBO</sub>	-20	-30	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	-10		Vdc
Collector Current — Continuous	Ic	-500		mAdc
Total Device Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	625 5.0		mW mW/°C
Total Device Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	1.5 12		Watts mW/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150		°C

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	°C/W

### **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage ( $I_C = -100 \mu Adc$ , $V_{BE} = 0$ ) MPSA62	V <sub>(BR)CES</sub>	-20 -30		Vdc	
MPSA63, MPSA64					
Collector Cutoff Current $(V_{CB}=-15 \text{ Vdc}, I_E=0)$ MPSA62 $(V_{CB}=-30 \text{ Vdc}, I_E=0)$ MPSA63, MPSA64	I <sub>CBO</sub>		-100 -100	nAdc	
Emitter Cutoff Current $(V_{EB} = -10 \text{ Vdc}, I_C = 0)$	I <sub>EBO</sub>	_	-100	nAdc	

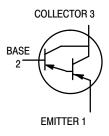
# MPSA62 MPSA63 MPSA64\*

MPSA55, MPSA56

For Specifications, See MPSA05, MPSA06 Data

\*ON Semiconductor Preferred Device





Preferred devices are ON Semiconductor recommended choices for future use and best overall value.

## MPSA62 MPSA63 MPSA64

# **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted) (Continued)

Characteristic		Symbol	Min	Max	Unit
ON CHARACTERISTICS <sup>(1)</sup>					
DC Current Gain		h <sub>FE</sub>			_
$(I_C = -10 \text{ mAdc}, V_{CE} = -5.0 \text{ Vdc})$	MPSA63		5,000	_	
	MPSA64		10,000	_	
	MPSA62		20,000	_	
$(I_C = -100 \text{ mAdc}, V_{CF} = -5.0 \text{ Vdc})$	MPSA63		10,000		
	MPSA64		20,000	_	
Collector–Emitter Saturation Voltage		V <sub>CE(sat)</sub>			Vdc
$(I_C = -10 \text{ mAdc}, I_B = -0.01 \text{ mAdc})$	MPSA62	, ,	_	-1.0	
$(I_C = -100 \text{ mAdc}, I_B = -0.1 \text{ mAdc})$	MPSA63, MPSA64		_	-1.5	
Base–Emitter On Voltage		V <sub>BE(on)</sub>			Vdc
$(I_C = -10 \text{ mAdc}, V_{CE} = -5.0 \text{ Vdc})$	MPSA62		_	-1.4	
$(I_C = -100 \text{ mAdc}, V_{CE} = -5.0 \text{ Vdc})$	MPSA63, MPSA64		_	-2.0	
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product <sup>(2)</sup>		f <sub>T</sub>	125	_	MHz
$(I_C = -100 \text{ mAdc}, V_{CE} = -5.0 \text{ Vdc}, f = 100 \text{ MHz})$	MPSA63, MPSA64				

<sup>1.</sup> Pulse Test: Pulse Width  $\leq$  300  $\mu s;$  Duty Cycle  $\leq$  2.0%.

<sup>2.</sup>  $f_T = |h_{fe}| \cdot f_{test}$ .

#### MPSA62 MPSA63 MPSA64

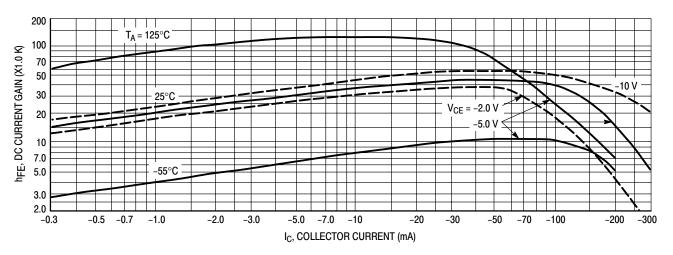


Figure 1. DC Current Gain

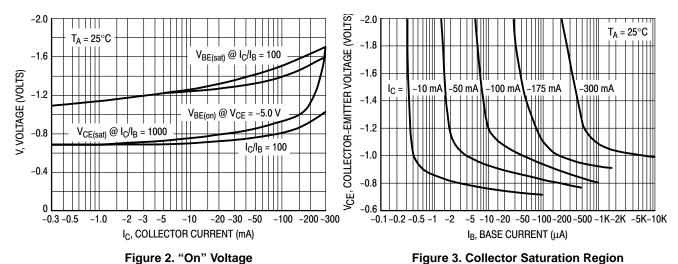


Figure 2. "On" Voltage

10

4.0

3.0

2.0

1.0

0.4

-1.0 -2.0

 $V_{CE} = -5.0 \text{ V}$ 

f = 100 MHz

. T<sub>A</sub> = 25°C

Ihfel, HIGH FREQUENCY CURRENT GAIN

-1000 100 μs 1.0 ms COLLECTOR CURRENT (mA) -300 -200 T<sub>A</sub> = 25°C -100 **CURRENT LIMIT** -50 THERMAL LIMIT SECOND BREAKDOWN LIMIT <u>ث</u> -20 (DUTY CYCLE ≤ 10%) MPSA63 -10 **∟** -1.0 -1K -4.0 -6.0 -10 -40 -60

IC, COLLECTOR CURRENT (mA) Figure 4. High Frequency Current Gain

-50

-100 -200

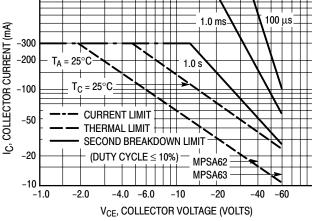
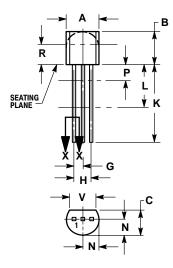


Figure 5. Active Region, Safe Operating Area

#### MPSA62 MPSA63 MPSA64

#### PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 ISSUE AL





STYLE 1: PIN 1. EMITTER 2. BASE

2. BASE 3. COLLECTOR

#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
   V14 FM 1092
- Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.
- CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN MAX	
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
ſ	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
Р		0.100		2.54
R	0.115		2.93	
٧	0.135		3.43	

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JAPAN: ON Semiconductor, Japan Customer Focus Center

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